International Rectifier

10TQ... SERIES

SCHOTTKY RECTIFIER

10 Amp

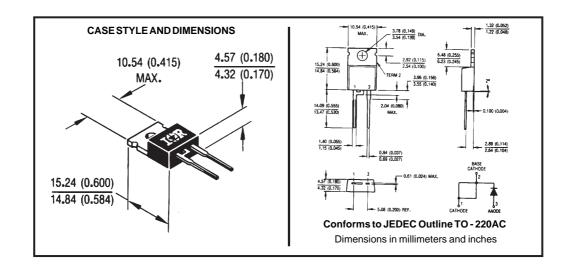
Major Ratings and Characteristics

Cha	racteristics	10TQ	Units
I _{F(AV)}	Rectangular waveform	10	А
V _{RRM}	range	35 to 45	V
I _{FSM}	@ tp = 5 µs sine	1050	А
V _F	@ 10 Apk, T _J =125°C	0.49	V
Т	range	-55 to 175	°C

Description/Features

The 10TQ Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175°C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- 175° CT_{.I} operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability



Voltage Ratings

Part number	10TQ035	10TQ040	10TQ045
V _R Max. DC Reverse Voltage (V)	25	40	4F
V _{RWM} Max. Working PeakReverse Voltage (V)	35	40	45

Absolute Maximum Ratings

Parameters		10TQ	Units	Conditions	
I _{F(AV)}	Max.AverageForwardCurrent *SeeFig.5	10	А	50% duty cycle @ T _C =151°C, rectangular wave form	
I _{FSM}	Max.PeakOneCycleNon-Repetitive	1050	Α	5μs Sine or 3μs Rect. pulse	Following any rated load condition and
	SurgeCurrent*SeeFig.7	280		10ms Sine or 6ms Rect. pulse	with rated V _{RRM} applied
E _{AS}	Non-RepetitiveAvalancheEnergy	13	mJ	T _J =25 °C, I _{AS} =2 Amps, L=6.5 mH	
I _{AR}	RepetitiveAvalancheCurrent	2	Α	Currentdecayinglinearlytozeroin1µsec	
				Frequency limited by T _J max. V _A	=1.5 x V _R typical

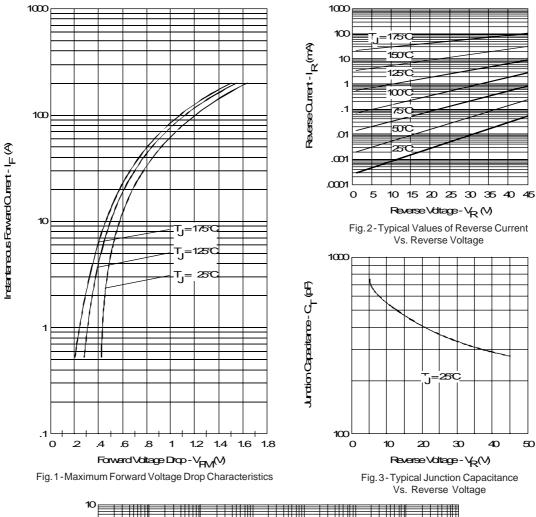
Electrical Specifications

	Parameters	10TQ	Units		Conditions
V _{FM}	Max. Forward Voltage Drop (1)	0.57	V	@ 10A	T, = 25 °C
	* See Fig. 1	0.67	V	@ 20A	1 _J = 23 C
		0.49	V	@ 10A	T _{,1} = 125 °C
		0.61	V	@ 20A	1, - 125 0
I _{RM}	Max. Reverse Leakage Current (1)	2	mA	T _J = 25 °C	\/ - rated \/
	* See Fig. 2	15	mA	T _J = 125 °C	$V_R = \text{rated } V_R$
C _T	Max. Junction Capacitance	900	pF	V _R = 5V _{DC} , (test signal range 100Khz to 1Mhz) 25 °C	
L _s	Typical Series Inductance	8.0	nΗ	Measured lead to lead 5mm from package body	
dv/dt	Max. Voltage Rate of Change	10,000	V/ µs		
	(Rated V _R)				

⁽¹⁾ Pulse Width < 300µs, Duty Cycle < 2%

Thermal-Mechanical Specifications

	Parameters		10TQ	Units	Conditions
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T _J	Max.JunctionTemperatureRange		-55to 175	°C	
T _{stg}	Max.StorageTemperatureRange		-55to175	°C	
R _{thJC}			2.0	°C/W	DCoperation *See Fig. 4
	toCase				
R _{thCS}	TypicalThermalResistance,Caseto		0.50	°C/W	Mountingsurface, smooth and greased
	Heatsink				
wt	ApproximateWeight		2(0.07)g	(oz.)	
Т	MountingTorque	Min.	6(5)	Kg-cm	
		Max.	12(10)	(lbf-in)	
	Case Style		TO-22	OAC	JEDEC



10
D=0.50
1 D=0.33
D=0.25
D=0.17
D=0.08
D=0.

Fig. 4-Maximum Thermal Impedance Z_{thJC} Characteristics

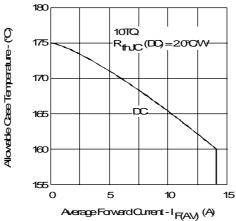


Fig. 5-Maximum Allowable Case Temperature
Vs. Average Forward Current

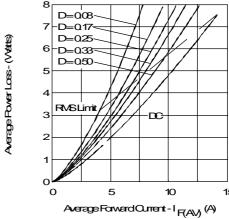


Fig. 6-Forward Power Loss Characteristics

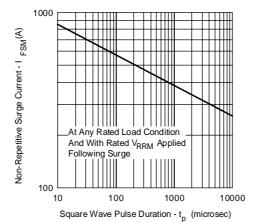


Fig. 7-Maximum Non-Repetitive Surge Current

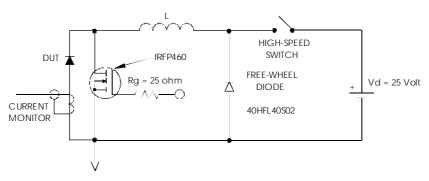


Fig. 8 - Unclamped Inductive Test Circuit